

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

# 2SK2162

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

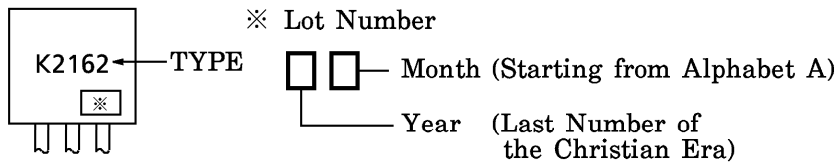
- High Breakdown Voltage :  $V_{DSS} = 180\text{ V}$
- High Forward Transfer Admittance :  $|Y_{fs}| = 0.7\text{ S (Typ.)}$
- Complementary to 2SJ338

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

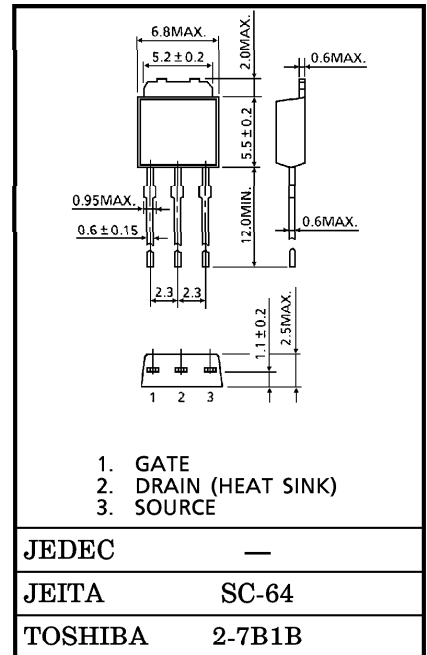
CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	180	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current (Note 1)	$I_D$	1	A
Power Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	20	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ\text{C}$

(Note 1) : Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

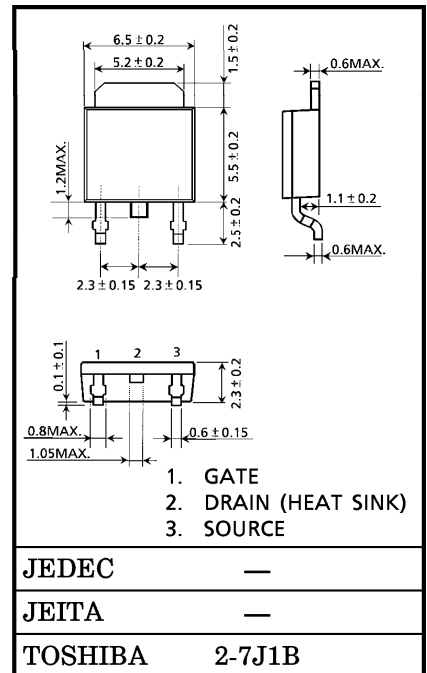
MARKING



Unit in mm



Weight : 0.36 g (Typ.)



Weight : 0.36 g

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GSS}$	$V_{DS} = 0, V_{GS} = \pm 20 \text{ V}$	—	—	$\pm 100$	nA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	180	—	—	V
Gate-Source Cut-off Current	$V_{GS(OFF)}$	$V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}$	1.4	—	2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D = 0.6 \text{ A}, V_{GS} = 10 \text{ V}$	—	1.7	3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 0.3 \text{ A}$	—	0.7	—	S
Input Capacitance	$C_{iss}$	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	170	—	pF
Output Capacitance	$C_{oss}$		—	45	—	
Reverse Transfer Capacitance	$C_{rss}$		—	17	—	

This transistor is the electrostatic sensitive device.  
Please handle with caution.

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000707EAA

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